

2SK3426

Silicon N-Channel Junction

For impedance conversion in low frequency

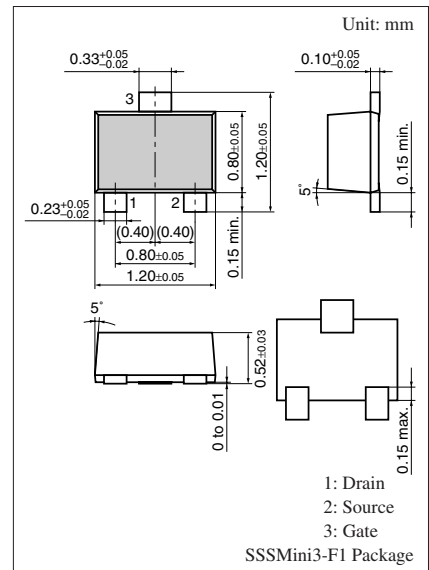
For electret capacitor microphone

■ Features

- High mutual conductance g_m
- Low noise voltage of NV

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Rating | Unit |
|-------------------------------|------------------|-------------|------------------|
| Drain-source voltage | V_{DSO} | 20 | V |
| Drain-gate voltage | V_{DGO} | 20 | V |
| Drain-source current | I_{DSO} | 2 | mA |
| Drain-gate current | I_{DGO} | 2 | mA |
| Gate-source current | I_{GSO} | 2 | mA |
| Allowable power dissipation | P_{D} | 100 | mW |
| Operating ambient temperature | T_{opr} | -20 to +80 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -55 to +125 | $^\circ\text{C}$ |



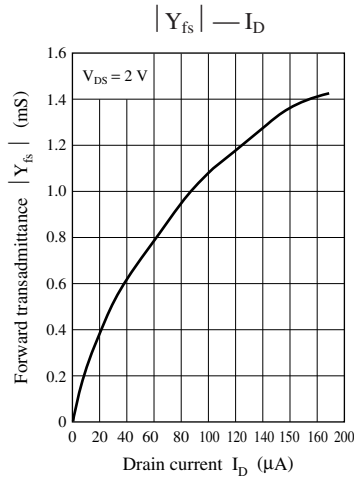
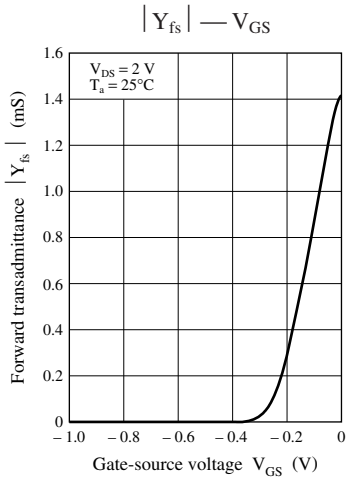
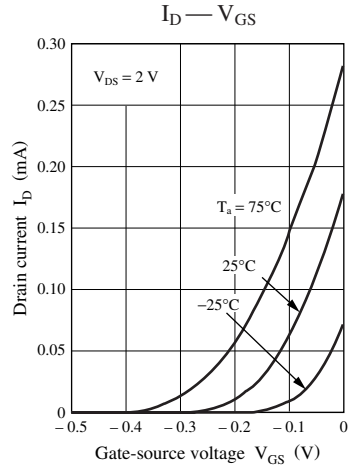
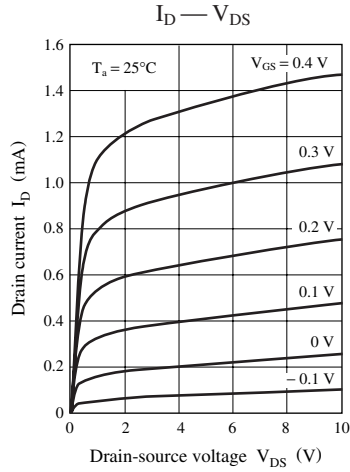
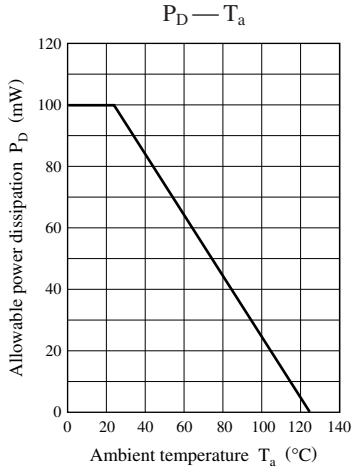
Marking Symbol: 4E

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|-------------------------|--------------------------------------|---|------|------|-----|---------------|
| Drain current | I_{D}^{*1} | $V_{\text{DS}} = 2.0 \text{ V}$, $R_{\text{D}} = 2.2 \text{ k}\Omega \pm 1\%$ | 100 | | 330 | μA |
| | I_{DSS} | $V_{\text{DS}} = 2.0 \text{ V}$, $R_{\text{D}} = 2.2 \text{ k}\Omega \pm 1\%$, $V_{\text{GS}} = 0$ | 107 | | 310 | |
| Mutual conductance | g_m | $V_{\text{D}} = 2.0 \text{ V}$, $V_{\text{GS}} = 0$, $f = 1 \text{ kHz}$ | 660 | 1300 | | μS |
| Noise voltage | NV | $V_{\text{D}} = 2.0 \text{ V}$, $R_{\text{D}} = 2.2 \text{ k}\Omega \pm 1\%$ $C_{\text{O}} = 5 \text{ pF}$, A-Curve | | | 8 | μV |
| Voltage gain | G_{V1} | $V_{\text{D}} = 2.0 \text{ V}$, $R_{\text{D}} = 2.2 \text{ k}\Omega \pm 1\%$ $C_{\text{O}} = 5 \text{ pF}$, $e_{\text{G}} = 10 \text{ mV}$, $f = 1 \text{ kHz}$ | -8.5 | -3.0 | | dB |
| | G_{V2} | $V_{\text{D}} = 12 \text{ V}$, $R_{\text{D}} = 2.2 \text{ k}\Omega \pm 1\%$ $C_{\text{O}} = 5 \text{ pF}$, $e_{\text{G}} = 10 \text{ mV}$, $f = 1 \text{ kHz}$ | -5.0 | -0.5 | | |
| | G_{V3} | $V_{\text{D}} = 1.5 \text{ V}$, $R_{\text{D}} = 2.2 \text{ k}\Omega \pm 1\%$ $C_{\text{O}} = 5 \text{ pF}$, $e_{\text{G}} = 10 \text{ mV}$, $f = 1 \text{ kHz}$ | -9.0 | -3.5 | | |
| | $\Delta G_{\text{V}} \cdot f ^{*2}$ | $V_{\text{D}} = 2.0 \text{ V}$, $R_{\text{D}} = 2.2 \text{ k}\Omega \pm 1\%$ $C_{\text{O}} = 5 \text{ pF}$, $e_{\text{G}} = 10 \text{ mV}$, $f = 1 \text{ kHz to } 70 \text{ Hz}$ | | 0 | 1.5 | |
| Voltage gain difference | $ G_{\text{V2}} - G_{\text{V1}} $ | | 0 | | 4.0 | dB |
| | $ G_{\text{V1}} - G_{\text{V3}} $ | | 0 | | 1.5 | |

Note) *1: I_{D} is assured for I_{DSS} .

*2: $\Delta |G_{\text{V}} \cdot f|$ is assured for AQL 0.065%. (the measurement method is used by source-grounded circuit.)



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